1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in an SOD323F (SC-90) very small and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 0.5 A
- Reverse voltage: V_R ≤ 40 V
- Low forward voltage typ. V_F = 550 mV
- Low reverse current typ. I_R = 1.5 μA
- · Very small and flat lead SMD plastic package
- AEC-Q101 qualified

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- · Reverse polarity protection
- Low power consumption applications
- Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le 135$ °C; square wave	-	-	0.5	A
V_R	reverse voltage	T _j = 25 °C	-	-	40	V
V _F	forward voltage	I_F = 500 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 25 °C	-	550	640	mV
I _R	reverse current	V _R = 40 V; pulsed; T _j = 25 °C	-	1.5	8	μA
		V _R = 40 V; pulsed; T _j = 125 °C	-	1	8	mA



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PMEG4005CEJ

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	1 2	1 - 2
2	А	anode	SOD323F	sym001

6. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
PMEG4005CEJ	SOD323F	plastic surface-mounted package; 2 leads	SOD323F					

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG4005CEJ	2F

2/13

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_R	reverse voltage	T _j = 25 °C		-	40	V
I _F	forward current	T _{sp} ≤ 130 °C; δ = 1		-	0.7	Α
I _{F(AV)}	average forward current	δ = 0.5 ; f = 20 kHz; $T_{sp} \le 135$ °C; square wave		-	0.5	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \delta \le 0.25$		-	2	А
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	8	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	415	mW
			[2]	-	715	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1][2]	-	-	300	K/W
			[1][3]	_	_	175	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[4]	-	-	45	K/W

^[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[4] Soldering point of cathode tab.

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

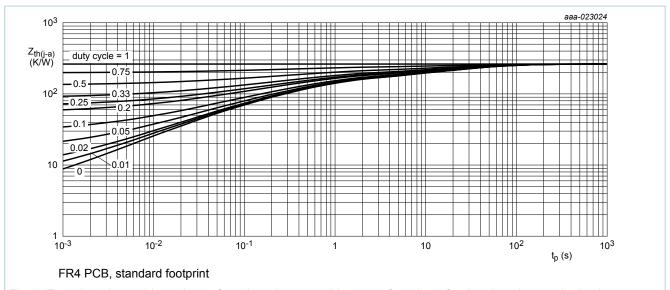


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

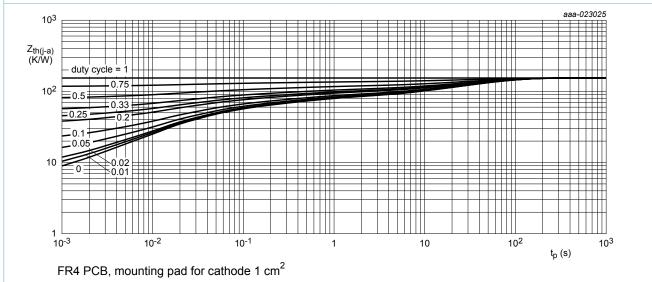


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)R}$	reverse breakdown voltage	$I_R = 1 \text{ mA}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$	40	-	-	V
V _F	forward voltage	$I_F = 10 \text{ mA}; t_p \le 300 \mu\text{s}; \delta \le 0.02 ;$ $T_j = 25 ^{\circ}\text{C}$	-	300	380	mV
		I_F = 100 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	390	470	mV
		I_F = 200 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	435	510	mV
		I_F = 300 mA; $t_p \le$ 300 μs; $δ \le$ 0.02 ; T_j = 25 °C	-	475	560	mV
		I_F = 400 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	515	600	mV
		I_F = 500 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 25 °C	-	550	640	mV
		I_F = 500 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = -40 °C	-	570	670	mV
		I_F = 500 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_j = 125 °C	-	520	610	mV
I _R	reverse current	V _R = 30 V; pulsed; T _j = 25 °C	-	1	5	μΑ
		V _R = 40 V; pulsed; T _j = 25 °C	-	1.5	8	μΑ
		V _R = 40 V; pulsed; T _j = 125 °C	-	1	8	mA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	24	-	pF
		V _R = 4 V; f = 1 MHz; T _j = 25 °C	-	13.5	-	pF
		V _R = 10 V; f = 1 MHz; T _j = 25 °C	-	9	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_i = 25 ^{\circ}\text{C}$	-	1.8	-	ns

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

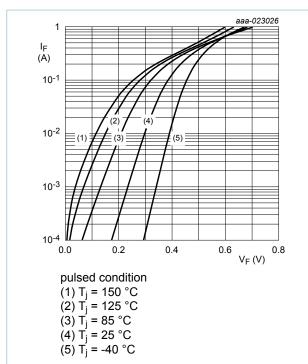


Fig. 3. Forward current as a function of forward voltage; typical values

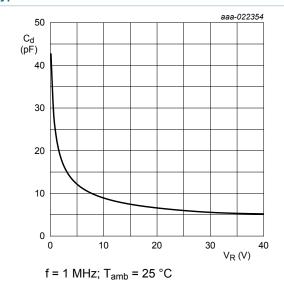


Fig. 5. Diode capacitance as a function of reverse voltage; typical values

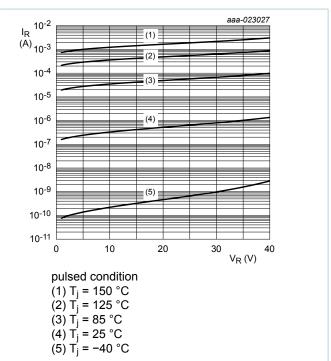
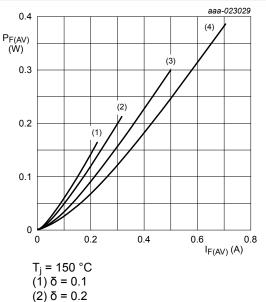


Fig. 4. Reverse current as a function of reverse voltage; typical values



 $(3) \delta = 0.5$

(2) $\delta = 1$ (DC)

Fig. 6. Average forward power dissipation as a function of average forward current; typical values

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

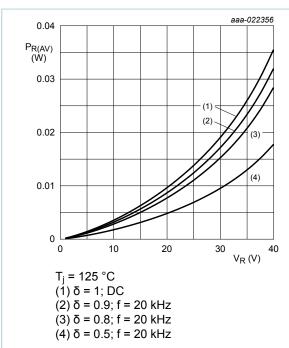


Fig. 7. Average reverse power dissipation as a function of reverse voltage; typical values

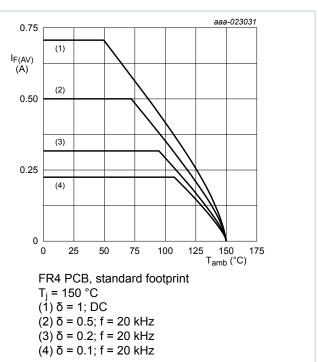
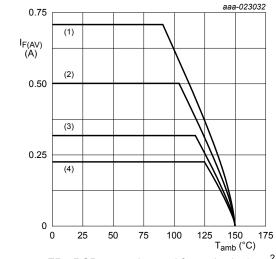


Fig. 8. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

 $T_j = 150 \, ^{\circ}C$

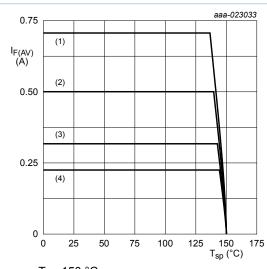
 $(1) \delta = 1; DC$

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz





 $T_j = 150 \,{}^{\circ}\text{C}$

 $(1) \delta = 1; DC$

(2) δ = 0.5; f = 20 kHz

(3) δ = 0.2; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

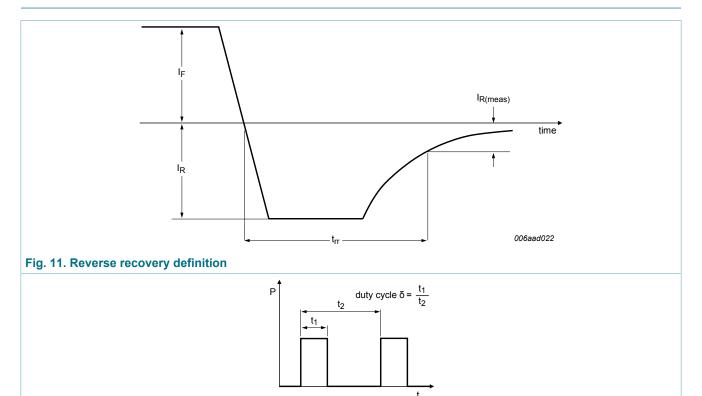
Fig. 10. Average forward current as a function of solder point temperature; typical values

7 / 13

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

11. Test information

Fig. 12. Duty cycle definition



The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

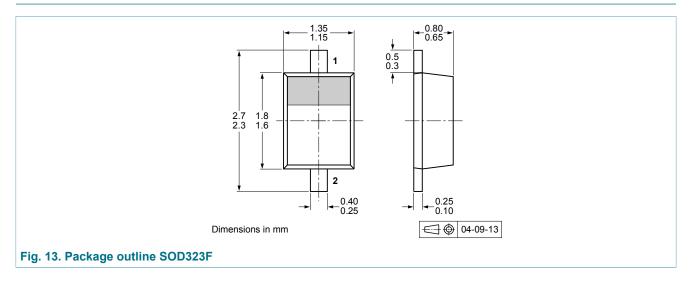
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Quality information

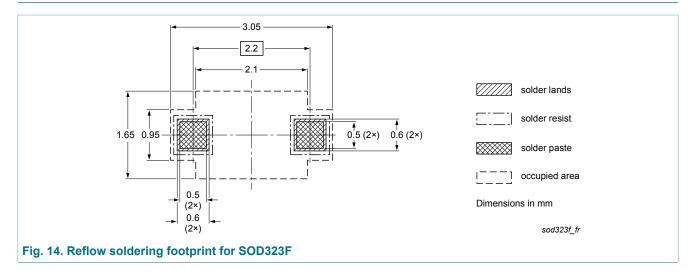
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

12. Package outline



13. Soldering



40 V, 0.5 A low VF MEGA Schottky barrier rectifier

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG4005CEJ v.1	20160512	Product data sheet	-	-

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PMEG4005CEJ

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMEG4005CEJ

40 V, 0.5 A low VF MEGA Schottky barrier rectifier

16. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	3
9.	Thermal characteristics	3
10.	Characteristics	5
11.	Test information	8
12.	Package outline	9
13.	Soldering	9
14.	Revision history	10
15.	Legal information	11

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